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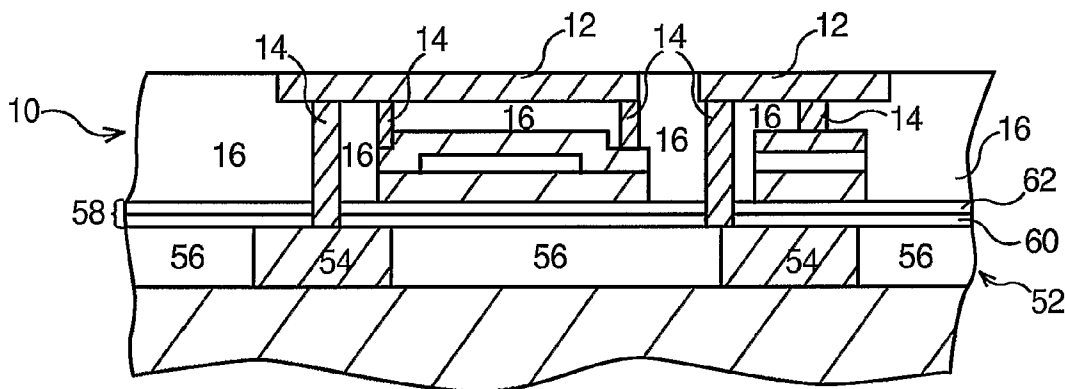
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(54) Title: METHOD OF FABRICATION OF THIN FILM RESISTOR WITH 0 CTR



(57) Abstract: A thin film resistor that has a substantially zero TCR is provided as well as a method for fabricating the same. The thin film resistor includes at least two resistor materials located over one another. Each resistor material has a different temperature coefficient of resistivity such that the effective temperature coefficient of resistivity of the thin film resistor is substantially 0 ppm/°C. The thin film resistor may be integrated into an interconnect structure or it may be integrated with a metal-insulator-metal capacitor (MIMCAP).

WO 2005/020250 A2